

BR600 - BR610

PRV : 50 - 1000 Volts

Io : 6.0 Amperes

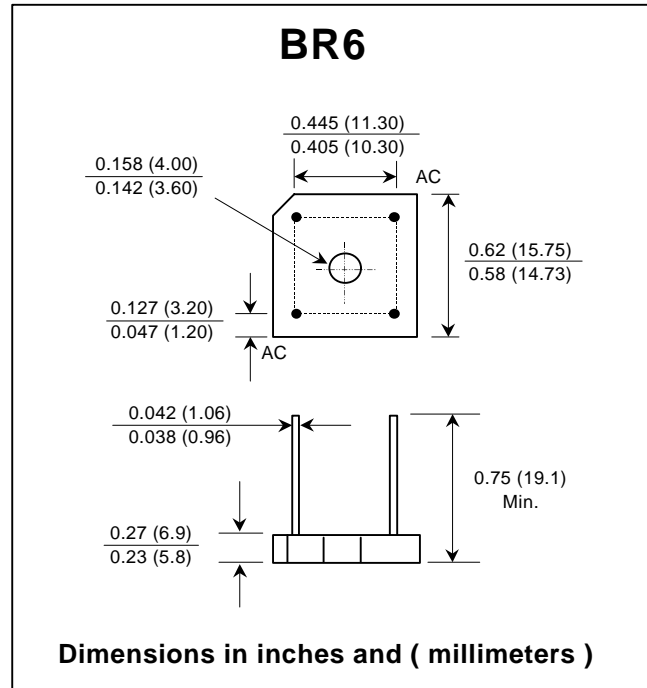
FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Ideal for printed circuit board
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL - STD 202 , Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any
- * Weight : 3.6 grams

SILICON BRIDGE RECTIFIERS



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	BR600	BR601	BR602	BR604	BR606	BR608	BR610	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Current $T_c=50^\circ C$	$I_{F(AV)}$	6.0							A
Peak Forward Surge Current, Single half sine wave Superimposed on rated load (JEDEC Method)	I_{FSM}	200							A
Current Squared Time at $t < 8.3$ ms.	I^2t	64							A^2S
Maximum Forward Voltage per Diode at $I_F = 3$ A.	V_F	1.0							V
Maximum DC Reverse Current at Rated DC Blocking Voltage	I_R	10							μA
	$I_{R(H)}$	200							μA
Typical Thermal Resistance (Note 1)	$R_{\theta JC}$	8.0							$^\circ C/W$
Operating Junction Temperature Range	T_J	- 40 to + 150							$^\circ C$
Storage Temperature Range	T_{STG}	- 40 to + 150							$^\circ C$

Notes :

1. Thermal Resistance from junction to case with units mounted on a 2.6" x 1.4" x 0.06" THK (6.5cm.x 3.5cm.x 0.15cm.) Al. Plate. Heatsink.

RATING AND CHARACTERISTIC CURVES (BR600 - BR610)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

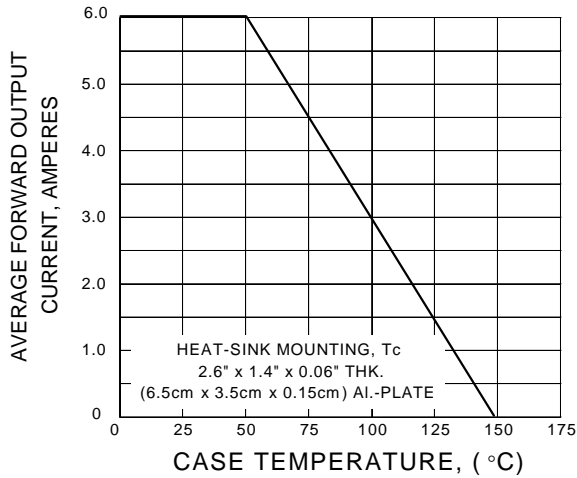


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

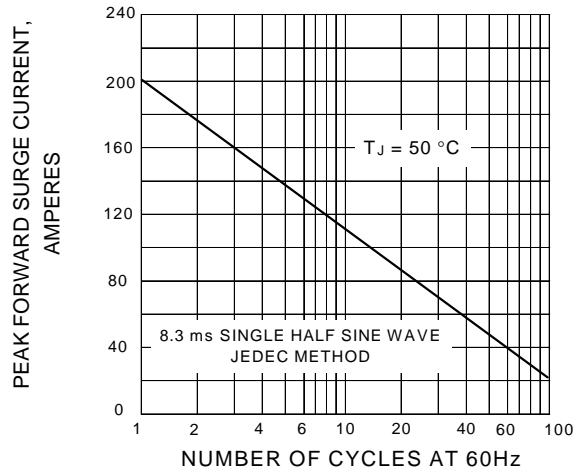


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

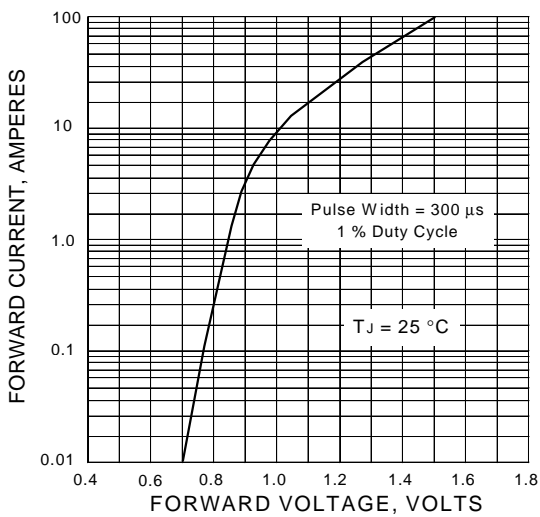


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE

